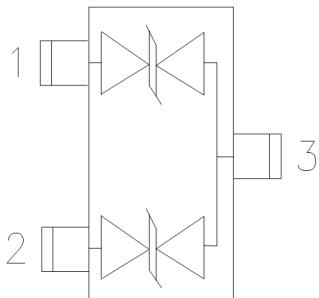


2-Line Bi-directional ESD Diode

Description

The EP3621T1 is a bi-directional TVS diode array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The EP3621T1 complies with the IEC 61000-4-2 (ESD) standard 4 with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a lead-free SOT-23 package. It is designed to protect components which are connected to data and transmission lines from voltage surges.

Circuit Diagram



Marking Diagram



Transparent top view

36C: Device Marking Code

Features

- * 450W peak pulse power (8/20 μs)
- * Protects two bi-directional lines
- * Ultra low leakage: nA level
- * Operating voltage: 36V
- * Low clamping voltage
- * Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC 61000-4-4 (EFT) 40A (5/50ns)
 - IEC 61000-4-5 (Lightning) 8A (8/20 μs)
- * RoHS Compliant
- * AEC-Q101 qualified (Automotive grade with suffix "Q".)
- * Exsemi technology

Applications

- * Cellular Handsets and Accessories
- * Notebooks and Handhelds
- * Portable Instrumentation
- * Set Top Box
- * Industrial Controls
- * Server and Desktop PC

Ordering Information

Part Number	Packaging	Reel Size
EP3621T1	3000/Tape & Reel	7 inch

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

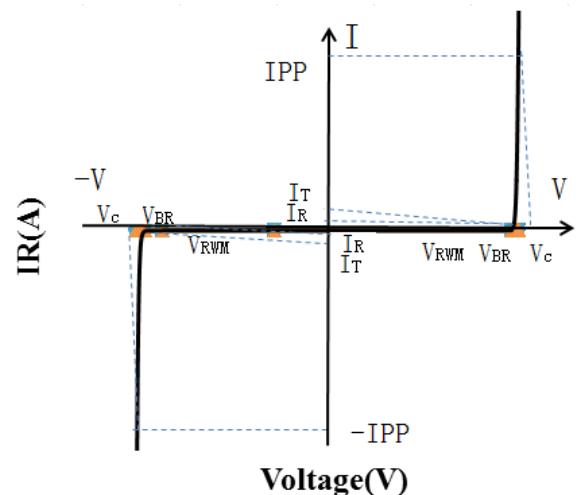
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	450	W
Peak Pulse Current (8/20μs)	IPP	8	A
ESD per IEC 61000-4-2 (Air)	VESD	±30	kV
ESD per IEC 61000-4-2		±30	
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

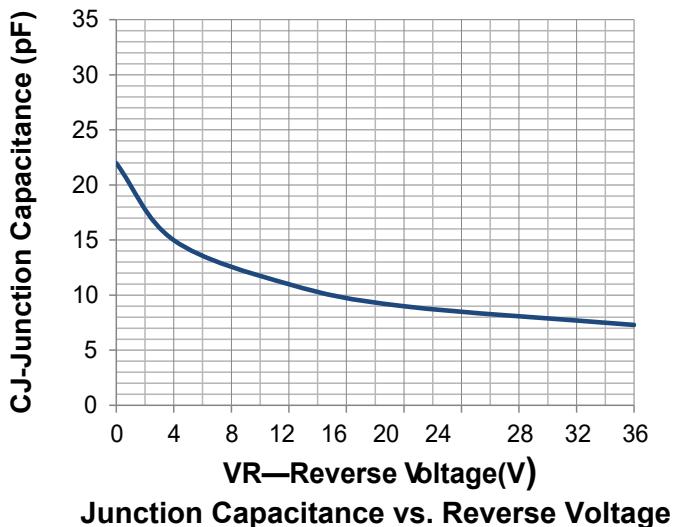
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	V _{RWM}				36	V
Breakdown Voltage	V _{BR}	I _T = 1mA	38.0	41.0	45.0	V
Reverse Leakage Current	I _R	V _{RWM} = 36V			0.5	µA
Clamping Voltage	V _C	I _{PP} = 1A (8 x 20μs pulse)		45	55	V
Clamping Voltage	V _C	I _{PP} = 8A (8 x 20μs pulse)		56	65	V
Junction Capacitance	C _J	V _R = 0V, f = 1MHz		20	40	pF

Portion Electronics Parameter

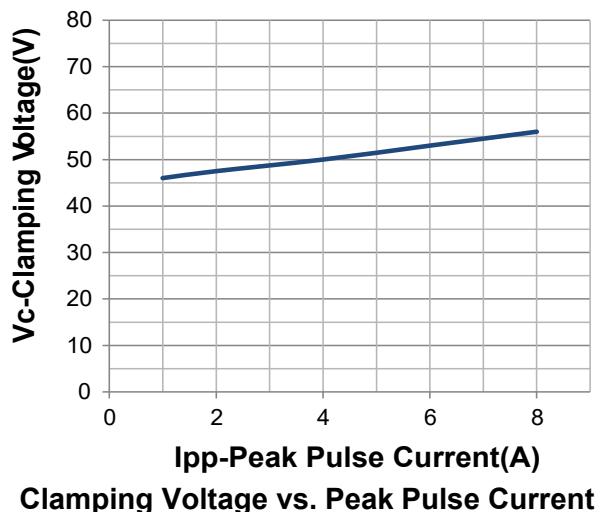
Symbol	Parameter
I _T	Test Current
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @I _C



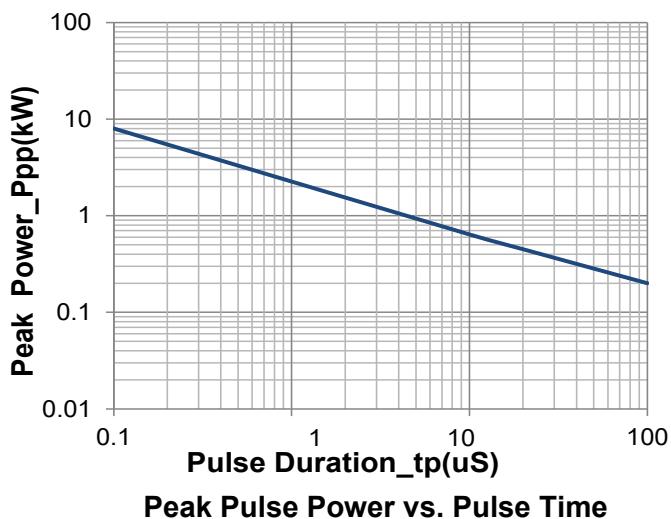
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



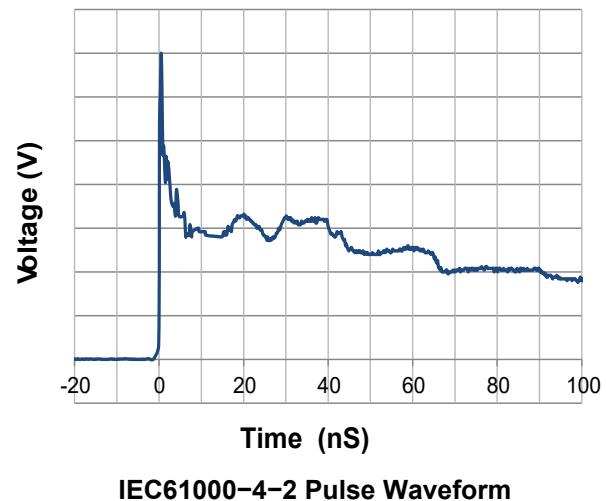
Junction Capacitance vs. Reverse Voltage



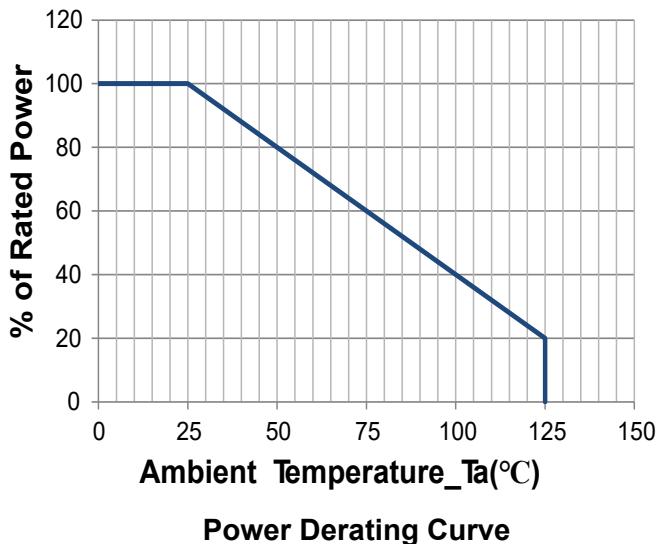
Clamping Voltage vs. Peak Pulse Current



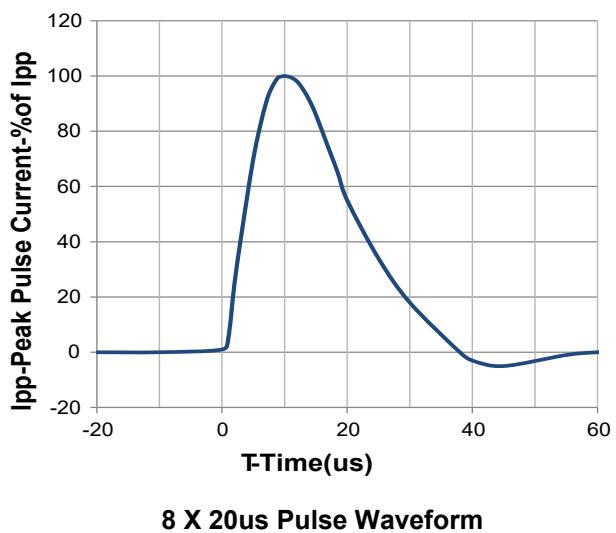
Peak Pulse Power vs. Pulse Time



IEC61000-4-2 Pulse Waveform

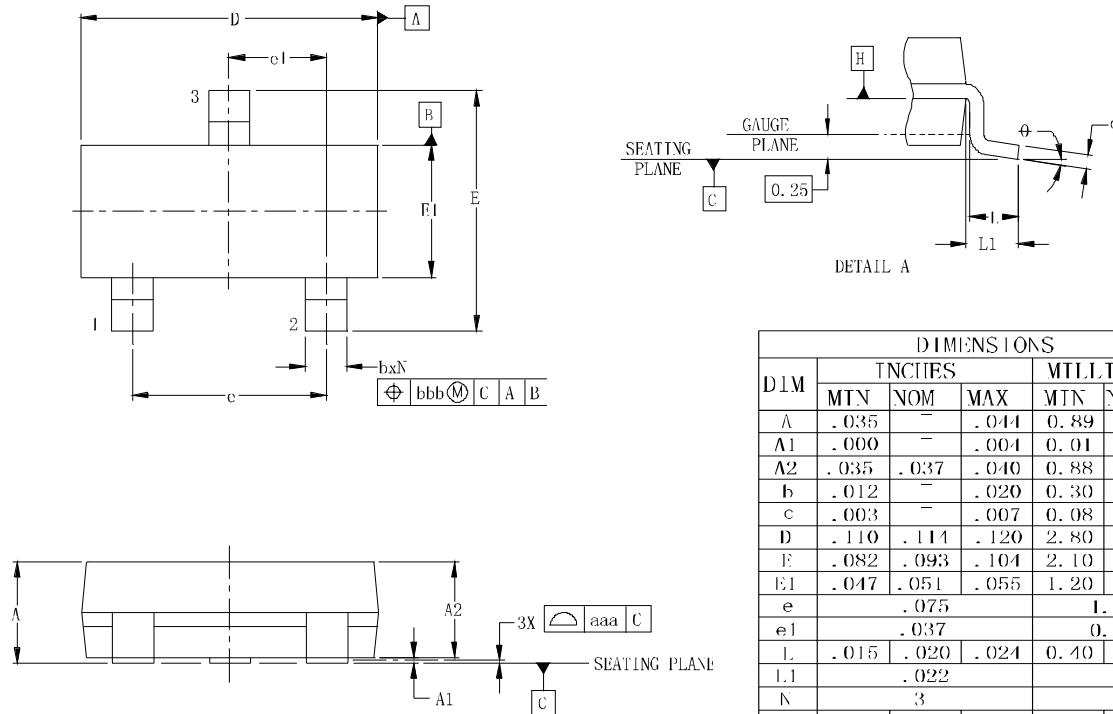


Power Derating Curve



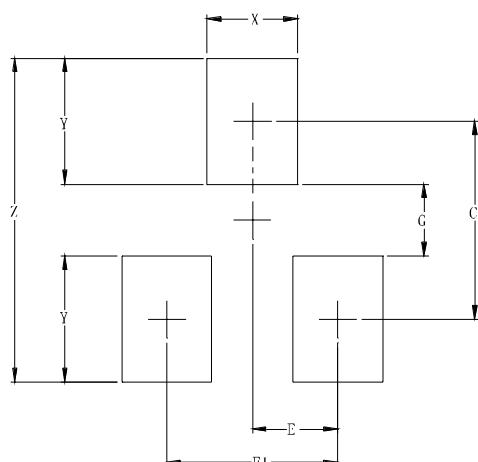
8 X 20us Pulse Waveform

SOT-23 Package Outline Drawing



DIM	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	.035	—	.044	0.89	—	1.12
A1	.000	—	.004	0.01	—	0.10
A2	.035	.037	.040	0.88	0.95	1.02
b	.012	—	.020	0.30	—	0.51
c	.003	—	.007	0.08	—	0.18
D	.110	.114	.120	2.80	2.90	3.04
E	.082	.093	.104	2.10	2.37	2.64
E1	.047	.051	.055	1.20	1.30	1.40
e	—	.075	—	1.90	BSC	—
e1	—	.037	—	0.95	BSC	—
L	.015	.020	.024	0.40	0.50	0.60
L1	—	.022	—	(0.55)	—	—
N	—	3	—	3	—	—
-θ	0°	—	8°	0°	—	8°
aaa	—	.001	—	0.10	—	—
bbb	—	.008	—	0.20	—	—

Suggested Land Pattern



DIMENSTONS		
DIM	INCHES	MILLIMETERS
C	.087	2.20
E	.037	0.95
E1	.075	1.90
G	.031	0.80
X	.039	1.00
Y	.055	1.40
Z	.141	3.60